

forming a hard mask layer disposed between the low dielectric constant material and the photoresist material;

A1end

forming an opening in the hard mask layer; and

removing said layer comprised of photoresist material with dimethyl sulfoxide.

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8. (Amended) A method of forming a semiconductor device, comprising:

providing a semiconductor substrate;

forming a layer comprised of a low dielectric constant material over said semiconductor substrate;

forming a hard mask layer over said low dielectric constant material;

A2

forming an opening in the hard mask layer;

forming a layer comprised of photoresist material over said layer comprised of said low dielectric constant material and over said hard mask layer;

patterning said layer comprised of photoresist material; and

removing said layer comprised of photoresist material with dimethyl sulfoxide.

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15. (Amended) A method of removing photoresist material from a semiconductor substrate, comprising:

A3

providing a semiconductor substrate having a layer comprised of a low dielectric constant material disposed thereover and a layer comprised of photoresist material disposed over said layer comprised of said low dielectric constant material; [and]

providing a hard mask layer disposed between said low dielectric constant material and said photoresist material;

forming an opening in said hard mask layer; and

placing said semiconductor substrate in an ultrasonic bath comprising dimethyl sulfoxide in liquid form, wherein said dimethyl sulfoxide removes said layer comprised of photoresist material.

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